

IN THE CLAIMS:

Kindly cancel claims 1 and 2 without prejudice or disclaimer. Kindly amend claim 5 as follows. A detailed listing of all claims is as follows.

Claims 1-2 (Canceled)

Claim 3 (Withdrawn): A method of forming an interlayer dielectric film in a semiconductor device, the method comprising:

forming a conductive layer pattern and an insulating film spacer on a sidewall of said conductive layer pattern through a common process;

removing said insulating film spacer in a region other than a contact plug formation region; and

forming an interlayer dielectric film on an entire surface of the semiconductor device.

Claim 4 (Withdrawn): The method according to claim 3, wherein said conductive layer pattern comprises one of a word line and a bit line.

Claim 5 (Currently Amended): A method of forming an interlayer dielectric film in a semiconductor device, the method comprising:

forming conductive layer patterns of a given pattern through a common process;

forming an interlayer dielectric film on an entire surface of the semiconductor device;

removing said interlayer dielectric film at a contact plug formation region; and

forming an insulating film spacer on a sidewall of said conductive layer patterns, which are exposed by the removing said interlayer dielectric film.

Claim 6 (Original): The method according to claim 5, wherein at least one of said conductive layer patterns comprises one of a word line and a bit line.

Claim 7 (Withdrawn): A method of forming an interlayer dielectric film in a semiconductor device, the method comprising:

forming conductive layer patterns and an insulating film spacer on a sidewall of said conductive layer patterns through a common process;

burying a conductive material between said conductive layer patterns;

removing said conductive material at a removal region such that said conductive material remains at remaining regions to form a contact plug; and

burying an interlayer dielectric film between said conductive layer patterns at said removal region.

Claim 8 (Withdrawn): The method according to claim 7, wherein at least one of said conductive layer patterns comprises one of a word line and a bit line.